Supporting Information

for

Superior Performance of an Ultrathin Pyridinic-Layered Micro-Structural Porous Silicon Anode with a Silicon Content Exceeding 99%

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1. Experimental

1.1. Material characterization.

The morphological study of all three samples was carried out by scanning electron microscope (SEM, Hitachi-SU8600, Japan) operated at 5 kV. Phases of the grafted porous silicon in PSi@PyC are investigated by the Transmission Electron Microscope (TEM, Tecnai by FEI, Field Electron and Ion Company, USA) with the energy-dispersive X-ray spectroscopy (EDS) analysis carried out at an acceleration voltage of 300 kV. An X-ray photoelectron spectrometer is used for (XPS Thermo Fisher Scientific, Nexsa). Topology and multi-particle statistics study for evaluating thickness uniformity was conducted by the Atomic Force Microscope (AFM) by Park System XE100 with AFM controller scanned in 3x3 µm in LV mode. The AFM sample preparation in performed in ethanol solvent by the spin coating at 300 RPM on a Si wafer of 2 x 2 cm. XPS data acquisition with the monochromatic source of low-power micro-focused Al K α radiation (hv =1486.6 eV) at a constant operating voltage of 15 kV. Whereas, full-range XPS spectra are carried out at an energy scan of 50 eV. The obtained XPS data is deconvoluted with XPSPEAK software (4.1 version, Ulvac-PHI, Japan) using Shirley type background and 100,101 Gauss-Lorentzian functions fitting with 80%/20% Gaussian/Lorentzian portion. Raman spectrometer (Monora 500i ANDOR) is operated at 633 nm wavelength to record Raman spectra of all three samples. Detailed investigation of the functional groups and bonding nature within as as-prepared samples are identified by the FT-IR (Bruker Vertex 70, USA). The ATR-FTIR spectra were recorded using a Perkin Elmer Spectrum Two FTIR Spectrometer, which is equipped with a LiTaO₃ detector and a PIKE Technologies MiracleTM Universal ATR accessory for single reflection sampling. The carbon content of the m-PSi@PyC is determined in the N2 atmosphere by the Thermogravimetric analysis (TGA) (SDT Q 600, TA Instrument Germany). The Brunauer-Emmett-Teller (BET) method is used to determine the specific surface area and pore size distribution of the materials using an adsorption analyzer (ASAP 2020 V3, Micromeritics Instrument Corporation, USA). The

crystalline phases of the Si in the materials are investigated by the XRD (Rigaku, Japan, Cu K_{∞} (λ = 1.5418 Å) radiation) operated in the 2 θ range of 10–90° at a scan rate of 5.0 °/min.

1.2 Calculations:

1.2.1 Kinetics study of Anodic and cathodic reactions:

The CV curves for the m-Si, m-PSi, and m-PSi @PyC at variable scan rates from 0.02 to 0.2 mV s⁻¹ are given in Fig. S6(a-c), respectively. The redox peak currents obtained from these CV curves of the prepared electrodes are utilized for the detailed kinetics study. The plot of peak current I_p vs the square root of scan rate ($V^{1/2}$) as shown in Fig. S6(d-f) is given for m-Si, m-PSi, and m-PSi@PyC, respectively. All the plots follow the linear relation with a regression coefficient ranging from 0.93 to 0.99 generally observed for the diffusion-controlled process at early scan rates¹. The redox peak currents and scan rate follow the following power equations (S1) and (S2).²

$$i = av^b \tag{S1}$$

$$\log i = \log a + b \log v \tag{S2}$$

Here, *v* represents the scan rate (mV s⁻¹), *i* is a peak current (mA), and a and b are the adjustable variables representing a storage mechanism of the anode materials.

1.2.2 Significance of b-values:

The value of *b* was obtained from the graph of log *i* vs log *v* for all the samples as shown in **Fig. S6(g-i)**. The *b* value has a range from 0.5 (a diffusion-controlled mechanism) to 1.0 (a capacitivecontrolled mechanism).³ Here, the b-values for both m-PSi and m-PSi@PyC for anodic and cathodic peak currents lie within 0.6 to 0.80, showing their mixed diffusion and capacitivecontrolled Li-ion storage mechanism. Inapposite m-Si obtained b-values of 0.49 and 0.41 (near 0.5) for its anodic and cathodic peak currents, suggesting that a diffusion-controlled Li-ion storage mechanism is prevalent in the m-Si.⁴

1.2.3 Capacity contribution calculation:

The following equations (S3) and (S4) are used for the calculation of the capacitive contribution.⁵

$$i = k_1 v + k_2 v^{1/2} \tag{S3}$$

$$\vec{u}/v^{2} = k_{1}v^{\frac{1}{2}} + k_{2}$$
(S3)

Here, k_1 and k_2 are the contribution constants, whereas k_{1v} and $k_2v^{(1/2)}$ indicate capacitive and diffusion current contributions, respectively. The k_1 value is calculated by the slope of $i/v^{1/2} vs v^{1/2}$ plot. The individual current contributions for each scan rate are calculated by the following equations, S5 and S6. The percentage of capacitive-controlled current contribution is given by the equation below (S5).⁶

$$\frac{k_1 v}{k_1 v + k_2 v^{\frac{1}{2}}} \times 100$$
(55)

Similarly, the percentage of diffusion-controlled current contribution (%) is expressed by equation (S6).

$$\frac{k_2 v^{\frac{1}{2}}}{k_1 v + k_2 v^{\frac{1}{2}}} \times 100$$



(S6)

Fig. S1. Thickness optimization: photographs of infiltration and grafting procedure for the a) 5%(w/v) PVPY solution, b) 10% PVPY solution, c) 15% PVPY solution, d) cyclic performance of the grafted samples, HRTEM images of the e) m-PSi@PyC (5%) and f) m-PSi@PyC (10%). **Note:** The yellow circled areas in (a)-3 and (b)-3 clearly show a smooth post-grafted surface showing successful grafting. However red circled areas in Figs. (c)-2 and 3 showed incomplete

infiltration due to high viscosity and subsequent poor grafting, leaving some portions of the m-PSi exposed at high temperatures.



Fig. S2. SEM-EDS mapping of m-Si (a-c), m-PSi (d-f) for Si and O contents and m-PSi@PyC (g-i) for Si, C, and O contents with the respective EDS layered images.



Fig. S3. SEM-EDS plots for m-Si (a), m-PSi (b), and m-PSi@PyC (c) for Si, C, and O contents.



Fig. S4. (a) AFM image (b)3D AFM image, (c) histogram of particle height distribution, (d) whole region line histogram of the m-PSi, (e) AFM image, (f) 3D AFM image, (g) histogram of particle height distribution, (h) whole region line histogram of the m-PSi@PyC.



Fig. S5. Surface composition comparison of the samples obtained by deconvoluted XPS Si 2*p* core spectra.



Fig. S6. Plausible thermolytic grafting mechanism for the bonding of pyridinic carbon at the interface of porous silicon composites: A: Infiltration, B: De-polymerization, C: Thermal grafting.



Fig. S7. Cyclic voltammetry curves (CV) for five cycles of (a) m-Si, (b) m-PSi, and (c) m-PSi@PyC.



Fig. S8. Cyclic voltammetry (CV) curves of (a) m-Si, (b) m-PSi, and (c) m-PSi@PyC at various scan rates (0.02–2.0 mV s⁻¹), relationship between peak current (i_p) and scan rate (v) plotted in logarithmic axes of (d) m-Si, (e) m-PSi and (f) m-PSi@PyC, corresponding plots of redox peak current density versus square root of scan rate of (g) m-Si, (h) m-PSi, and (i) m-PSi@PyC.



Fig. S9. Long cyclic performance of the m-PSi@PyC at higher current densities of 2 A g^{-1} and 5 A g^{-1} .

Active	5 th cycle specific	150th Cycle Specific	Capacity retention	
materials	capacity (mAh g ⁻¹) at	capacity (mAh g ⁻¹)	(%)	
	0.1 Ag ⁻¹			
	(After SEI formation)			
m- Si	2165.16	150.89	6.96	
m-PSi	2638.64	1012.56	38.37	
m-PSi@PyC	3037.10	2150.82	70.81	
Active	5th cycle specific	100 th Cycle Specific	Capacity retention	
materials	capacity (mAh g-1) at	capacity (mAh g ⁻¹)	(%)	
	0.5 Ag ⁻¹			
	(After SEI formation)			
m-PSi	2103.48	718.04	34.13	
m-PSi@PyC	2837.10	1720.71	60.65	

Table S1. Cyclic performances and retentions of the m-Si, m-PSi, and m-PSi@PyC samples

Table S2. Fitted circuit and the corresponding data of the impedance spectra of Li cells employing the as-prepared samples as anodes before and after 150th cycles



Samples		$R_{ m e}\left(\Omega ight)$	$R_{ m SEI}\left(\Omega ight)$	$R_{ m ct}\left(\Omega ight)$
m-Si	Before cycling	3.90	168.52	158.57
	Post cycling	5.53	352.24	253.23
m-PSi	Before cycling	2.39	158.62	108.98
	Post cycling	4.98	242.15	224.48
PSi@PyC	Before cycling	1.75	78.25	68.96
	Post cycling	4.65	189.25	170.5
	Post cycling	4.65	189.25	170.5



Fig. S10. a) Optimization of the N/P ratio in the NCM811/m-PSi@PyC full cell assemblies b) the electrolyte consumption in the corresponding full cell assemblies.



Fig. S11. FTIR Spectra of the lithiated and de-lithiated m-PSi@PyC anode material.

Observed wavenumbe r (cm ⁻¹)	Peak summary		References
3530-3640	<i>v</i> (О-Н)	Si-OH	[7]
3200-3600	<i>v</i> (N-H)	Hydrogenated Pyridinic or Pyrrolic N groups	[8]
2800-3000	v (C-H)	Aliphatic C-H	[9]
2120-2040	Li-N=C	Li-N-C(sp ²) species	[10]
1790-1707	v (C=O)	Alkyl carbonate ROCOOLi	[11]
1428–1340	v (C=O)	Carbonate salt Li ₂ CO ₃	[12]
1223–1342	v (O-C–O)	Alkyl carbonate ROCO ₂ Li	[13]
1060–972	v (Si–O)	Silicon oxide	[14]
1219–1105	v(C–O)	R-CO ₂ -Li salt	[6]
890-830	γ (C–H)	Aromatic carbon (-C ₆ H ₅)	[15]

Table S3. Detailed absorption peaks in the Fourier transform infrared (FT-IR) spectra of m-

PSi@PyC composites after lithiation and delithiation



Fig. S12. Rate capability comparison of as-prepared m-PSi and m-PSi@PS samples at a current density ranging from 0.1 A to 4 A g⁻¹.



Fig. S13. Grafting results of the m-PSi@PANI-C: a) 10% (w/v) PANI solution in NMP, b) Insoluble PANI residue c) incomplete infiltration of PANI in the m-PSi due to its limited solubility in organic solvents leaving it on the surface as shown in yellow rings d) incomplete grafting causing PANI residues remain ungrafted on the m-PSi surface (yellow ring).



Fig. S14. Prior cycling digital photographs of the electrode surfaces for (a) m-PSi (a) and for (b) m-PSi@PyC, post-cycled digital photographs of the (c) m-PSi and (d) m-PSi@PyC electrodes.

Observed Wavenumber (cm ⁻¹)	Peak sumn	nary	References
1657–1596	$v_{as}(C=O)$	Alkyl carbonate ROCOOLi	[11,15]
1550–1531	v (C=O)	Alkyl carboxylate	[15,16]
1453–1350	v (C=O)	Carbonate salt LiO–CO–OLi	[17]
1260–1330	v (C–F)	Fluoroalkyl	[18]
1130-1000	v (Si–O)	Silicon oxide	[19]
950-840	γ (C–O)	Carbonate salt	[20,21]
850-830	v (P–F)	Porous fluorides	[6]
570-526	v (Li–F)	Lithium fluoride	[22]
614–590	v (Si–F)	Lithium hexafluoro silicate	[23]

Table S4. Detailed absorption peaks in the Fourier transform infrared (FT-IR) spectra of post-cycled composites

* v: stretching vibration, v_{as} : asymmetric stretching vibration, γ : out-of-plane bending vibration



Fig. S15. XPS survey scan of (a) m-PSi, deconvoluted XPS (b) C 1s, (c) P2p, (d) F1s (e) Li 1s,(f) O 1s core spectra of m-PSi, (g) XPS survey scan, (h) C 1s, (i) P2p 1s, (j) F 1s (k) Li 1s, (l) O1scorespectraofm-PSi@PyC.

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